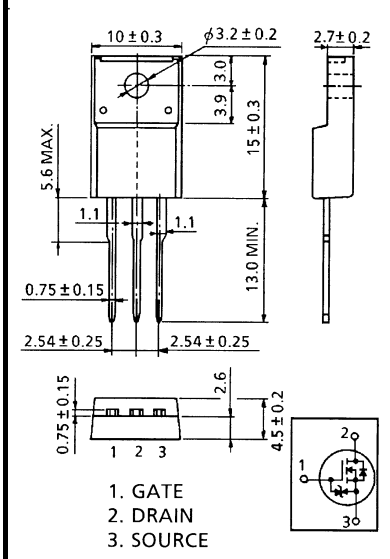
2SK2700

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- Low drain–source ON resistance : $R_{DS\ (ON)}$ = 3.7 Ω (typ.)
- High forward transfer admittance : $|Y_{fs}|$ = 2.6 S (typ.)
- Low leakage current : I_{DSS} = 100 μA (max) (V_{DS} = 720 V)
- Enhancement mode : V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_D = 1 mA)

Unit: mm



JEDEC	—
JEITA	SC-67
TOSHIBA	2-10R1B

Weight: 1.9 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain–source voltage		V_{DSS}	900	V
Drain–gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	900	V
Gate–source voltage		V_{GSS}	±30	V
Drain current	DC (Note 1)	I_D	3	A
	Pulse (Note 1)	I_{DP}	9	A
Drain power dissipation (Tc = 25°C)		P_D	40	W
Single pulse avalanche energy (Note 2)		E_{AS}	295	mJ
Avalanche current		I_{AR}	3	A
Repetitive avalanche energy (Note 3)		E_{AR}	4	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th\ (ch–c)}$	3.125	°C / W
Thermal resistance, channel to ambient	$R_{th\ (ch–a)}$	62.5	°C / W

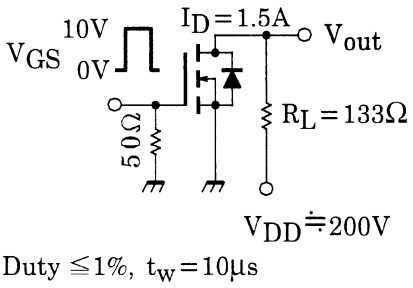
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 60.0 mH, R_G = 25 Ω, I_{AR} = 3 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.
Please handle with caution.

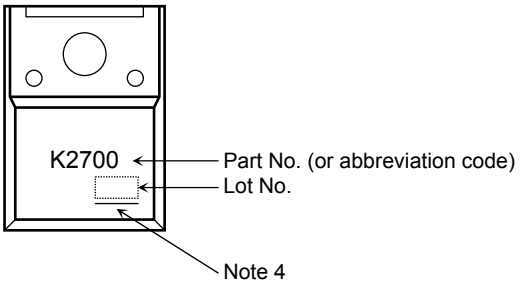
Electrical Characteristics (Ta = 25°C)

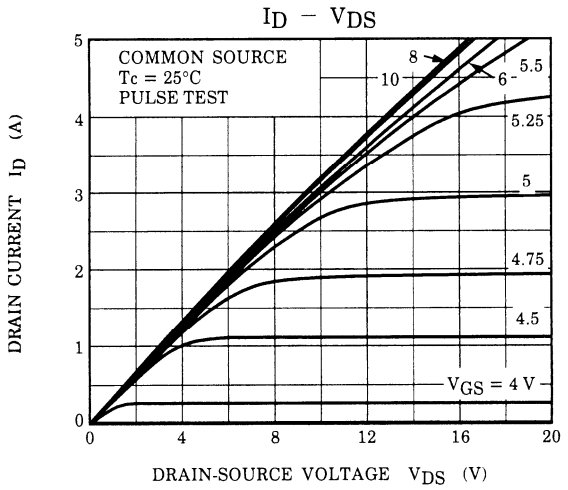
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	—	—	±10	μA
Gate–source breakdown voltage		$V_{(BR)\ GSS}$	I_G = ±10 μA, V_{DS} = 0 V	±30	—	—	V
Drain cut–off current		I_{DSS}	V_{DS} = 720 V, V_{GS} = 0 V	—	—	100	μA
Drain–source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	900	—	—	V
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	2.0	—	4.0	V
Drain–source ON resistance		$R_{DS\ (ON)}$	V_{GS} = 10 V, I_D = 1.5 A	—	3.7	4.3	Ω
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 20 V, I_D = 1.5 A	0.65	2.6	—	S
Input capacitance		C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	—	750	—	pF
Reverse transfer capacitance		C_{rss}		—	10	—	
Output capacitance		C_{oss}		—	70	—	
Switching time	Rise time	t_r		—	15	—	ns
	Turn–on time	t_{on}		—	55	—	
	Fall time	t_f		—	30	—	
	Turn–off time	t_{off}		—	110	—	
Total gate charge (gate–source plus gate–drain)		Q_g	V_{DD} ≈ 400 V, V_{GS} = 10 V, I_D = 3 A	—	25	—	nC
Gate–source charge		Q_{gs}		—	13	—	
Gate–drain (“miller”) Charge		Q_{gd}		—	12	—	

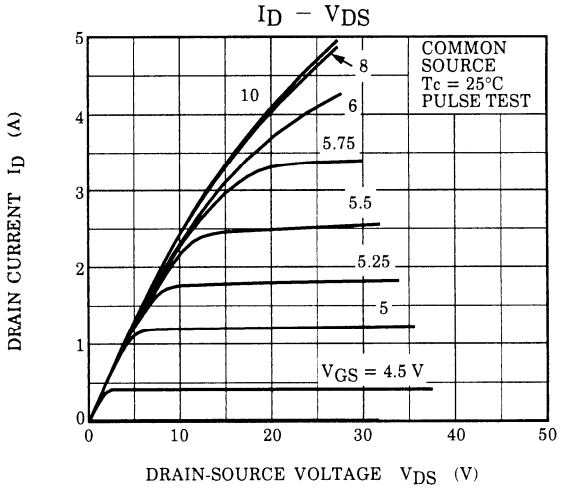
Source–Drain Ratings and Characteristics (Ta = 25°C)

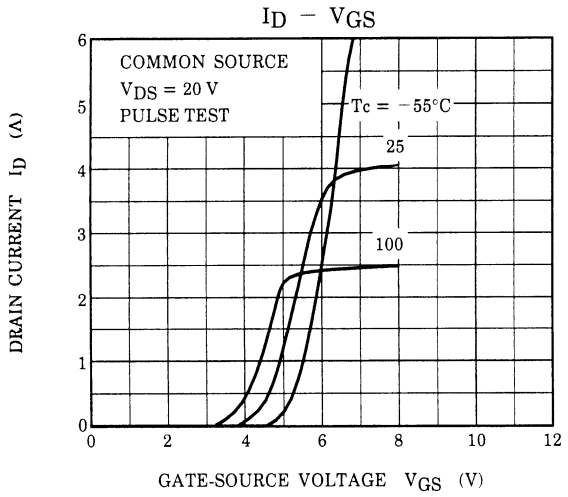
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	3	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	9	A
Forward voltage (diode)	V_{DSF}	I_{DR} = 3 A, V_{GS} = 0 V	—	—	−1.9	V
Reverse recovery time	t_{rr}	I_{DR} = 3 A, V_{GS} = 0 V dI_{DR} / dt = 100 A / μs	—	1100	—	ns
Reverse recovery charge	Q_{rr}		—	7.2	—	μC

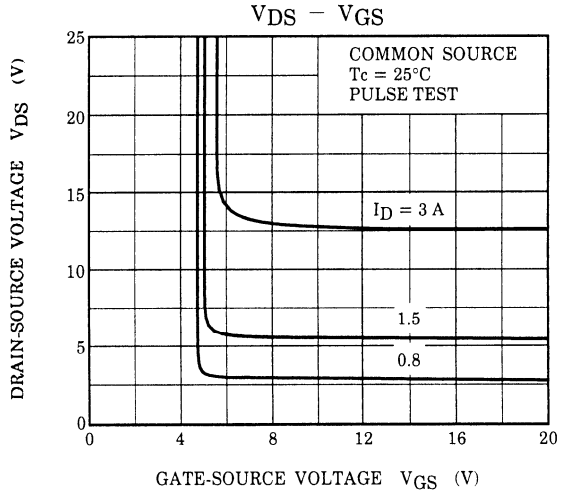
Marking

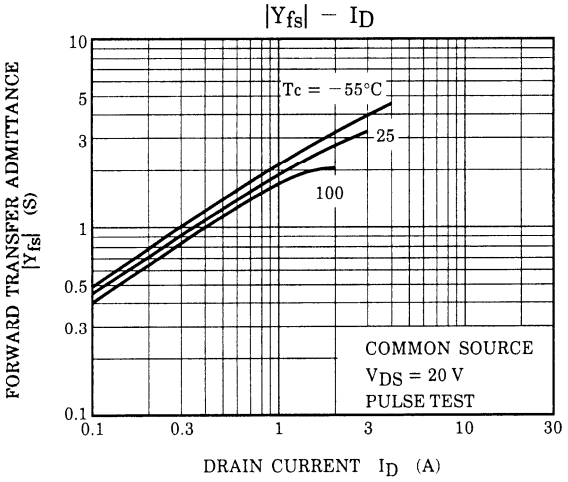


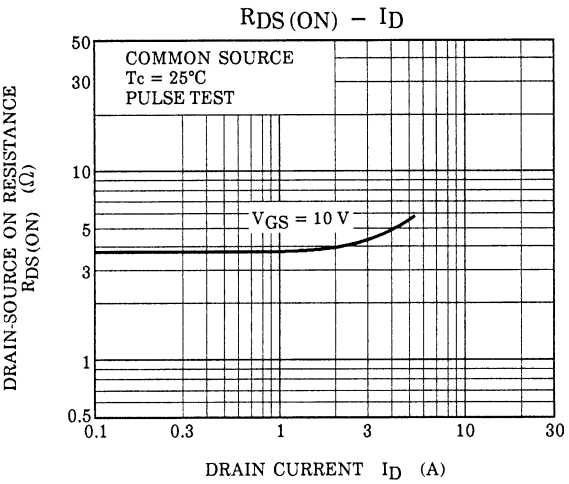

I_D – V_{DS}
COMMON SOURCE
Tc = 25°C
PULSE TEST
8
10
6
5.5
5.25
5
4.75
4.5
V_{GS} = 4 V
DRAIN CURRENT I_D (A)
DRAIN-SOURCE VOLTAGE V_{DS} (V)


I_D – V_{DS}
COMMON SOURCE
Tc = 25°C
PULSE TEST
8
10
6
5.75
5.5
5.25
5
V_{GS} = 4.5 V
DRAIN CURRENT I_D (A)
DRAIN-SOURCE VOLTAGE V_{DS} (V)


I_D – V_{GS}
COMMON SOURCE
V_{DS} = 20 V
PULSE TEST
Tc = −55°C
25
100
DRAIN CURRENT I_D (A)
GATE-SOURCE VOLTAGE V_{GS} (V)


V_{DS} – V_{GS}
COMMON SOURCE
Tc = 25°C
PULSE TEST
I_D = 3 A
1.5
0.8
DRAIN-SOURCE VOLTAGE V_{DS} (V)
GATE-SOURCE VOLTAGE V_{GS} (V)


$|Y_{fs}|$ – I_D
Tc = −55°C
25
100
COMMON SOURCE
V_{DS} = 20 V
PULSE TEST
FORWARD TRANSFER ADMITTANCE $|Y_{fs}|$ (S)
DRAIN CURRENT I_D (A)


$R_{DS(ON)}$ – I_D
COMMON SOURCE
Tc = 25°C
PULSE TEST
V_{GS} = 10 V
DRAIN-SOURCE ON RESISTANCE $R_{DS(ON)}$ (Ω)
DRAIN CURRENT I_D (A)